

■ **Features**

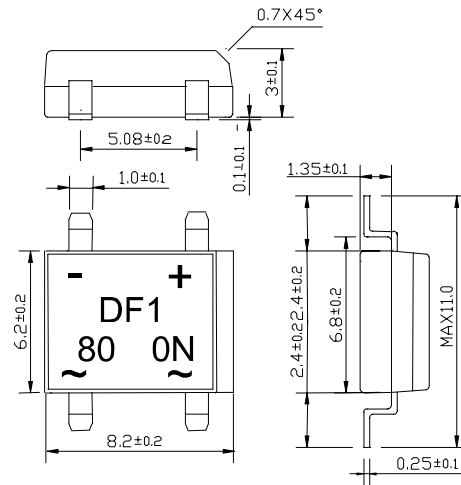
- I_o 1.0A
- V_{RRM} 200V~1000V
- Glass passivated chip
- High surge forward current capability
- Supersmall size

■ **Applications**

- General purpose 1 phase Bridge rectifier applications

Outline Dimensions and Mark

Unit: mm



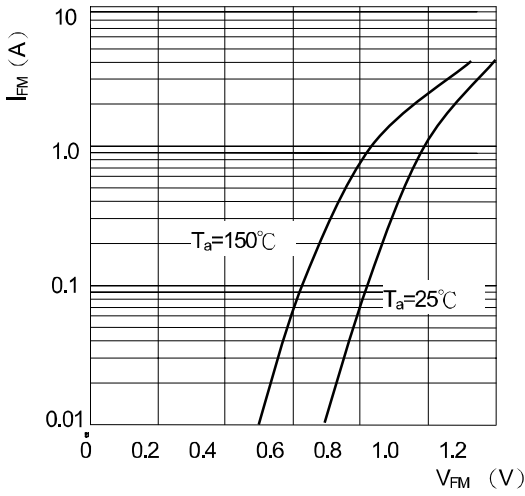
■ **Limiting Values (Absolute Maximum Rating)**

Item	Symbol	Unit	Conditions	DF1				
				20	40	60	80	100
Storage Temperature	T_{stg}	°C		-40 ~ +150				
Junction Temperature	T_j	°C		+150				
Repetitive Peak Reverse Voltage	V_{RRM}	V		200	400	600	800	1000
Average Rectified Output Current	I_o	A	50Hz sine wave, R- load, $T_a=25^\circ\text{C}$	On glass-epoxi substrate		1		
Surge(Non-repetitive)Forward Current	I_{FSM}	A	50Hz sine wave, 1 cycle, $T_a=25^\circ\text{C}$	30				

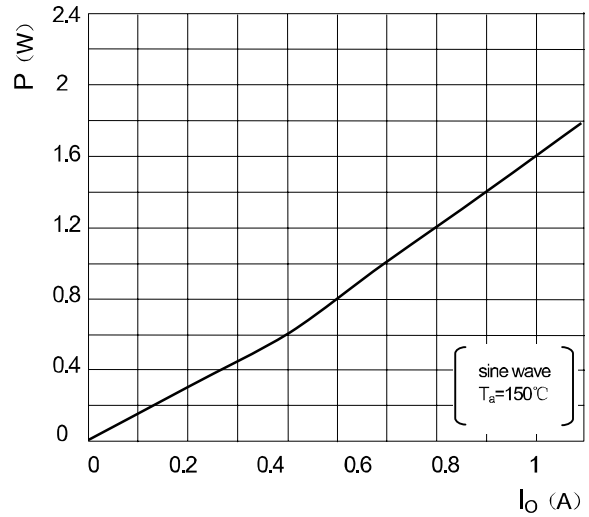
■ **Electrical Characteristics** ($T_a=25^\circ\text{C}$ Unless otherwise specified)

Item	Symbol	Unit	Test Condition	Max
Peak Forward Voltage	V_{FM}	V	$I_{FM}=0.5\text{A}$, Pulse measurement, Rating of per diode	1.05
Peak Reverse Current	I_{RRM1}	μA	$V_{RM}=V_{RRM}$, Pulse measurement, Rating of per diode	10
Thermal Resistance	$R_{\theta J-A}$	°C/W	Between junction and ambient ,On alumina substrate	76
			Between junction and ambient ,On glass-epoxi substrate	134
	$R_{\theta J-L}$		Between junction and lead	20

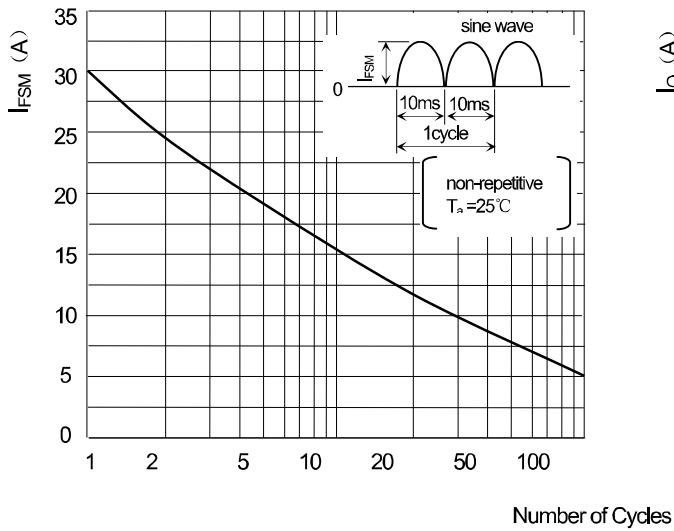
■ Characteristics(Typical)



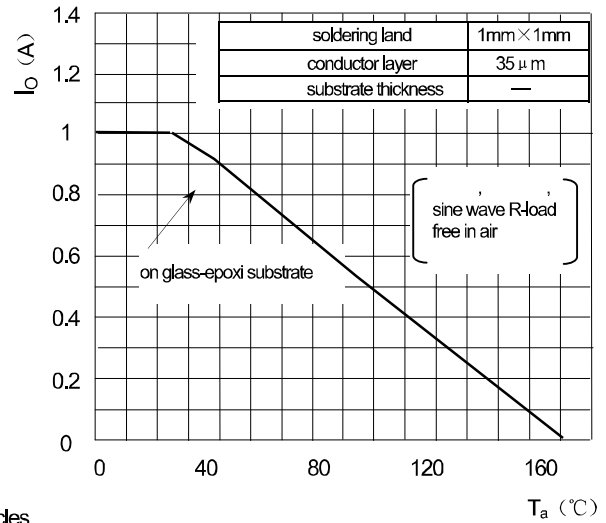
Forward Characteristics



P- I_o Curve



Surge Forward Current Capability



I_o - T_a Curve